

Thyristor Module

$$V_{RRM} = 1800\text{ V}$$

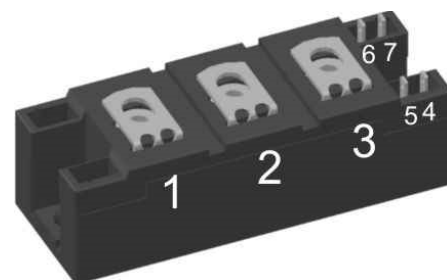
$$I_{TAV} = 2 \times 216\text{ A}$$

$$V_T = 1.1\text{ V}$$

Common Cathode

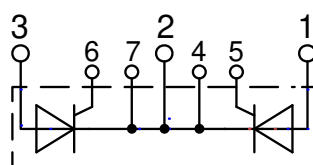
Part number

MCK200-18io1



Backside: isolated

 E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al₂O₃-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: Y4

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

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Thyristor				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1900	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1800	V
$I_{R/D}$	reverse current, drain current	$V_{R/D} = 1800\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			400	μA
		$V_{R/D} = 1800\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$			15	mA
V_T	forward voltage drop	$I_T = 200\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.20	V
		$I_T = 400\text{ A}$				1.52	V
		$I_T = 200\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1.10	V
		$I_T = 400\text{ A}$				1.50	V
I_{TAV}	average forward current	$T_C = 85^{\circ}\text{C}$	$T_{VJ} = 125^{\circ}\text{C}$			216	A
$I_{T(RMS)}$	RMS forward current	180° sine				340	A
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 125^{\circ}\text{C}$			0.80	V
r_T	slope resistance					1.4	m Ω
R_{thJC}	thermal resistance junction to case					0.13	K/W
R_{thCH}	thermal resistance case to heatsink				0.05		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$			770	W
I_{TSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			8.00	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			8.64	kA
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 125^{\circ}\text{C}$			6.80	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			7.35	kA
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			320.0	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			310.5	kA ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 125^{\circ}\text{C}$			231.2	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			224.4	kA ² s
C_J	junction capacitance	$V_R = 400\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		366		pF
P_{GM}	max. gate power dissipation	$t_p = 30\text{ }\mu\text{s}$	$T_C = 125^{\circ}\text{C}$			120	W
		$t_p = 500\text{ }\mu\text{s}$				60	W
P_{GAV}	average gate power dissipation					20	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 125^{\circ}\text{C}; f = 50\text{ Hz}$ repetitive, $I_T = 600\text{ A}$				100	A/ μs
		$t_p = 200\text{ }\mu\text{s}; di_G/dt = 0.5\text{ A}/\mu\text{s};$ $I_G = 0.5\text{ A}; V = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 200\text{ A}$				500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^{\circ}\text{C}$			1000	V/ μs
		$R_{GK} = \infty$; method 1 (linear voltage rise)					
V_{GT}	gate trigger voltage	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			2	V
			$T_{VJ} = -40^{\circ}\text{C}$			3	V
I_{GT}	gate trigger current	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			150	mA
			$T_{VJ} = -40^{\circ}\text{C}$			220	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125^{\circ}\text{C}$			0.25	V
I_{GD}	gate non-trigger current					10	mA
I_L	latching current	$t_p = 30\text{ }\mu\text{s}$	$T_{VJ} = 25^{\circ}\text{C}$			200	mA
		$I_G = 0.5\text{ A}; di_G/dt = 0.5\text{ A}/\mu\text{s}$					
I_H	holding current	$V_D = 6\text{ V}$ $R_{GK} = \infty$	$T_{VJ} = 25^{\circ}\text{C}$			150	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}\text{C}$			2	μs
		$I_G = 0.5\text{ A}; di_G/dt = 0.5\text{ A}/\mu\text{s}$					
t_q	turn-off time	$V_R = 100\text{ V}; I_T = 300\text{ A}; V = \frac{2}{3} V_{DRM}$ $T_{VJ} = 100^{\circ}\text{C}$ $di/dt = 10\text{ A}/\mu\text{s}$ $dv/dt = 50\text{ V}/\mu\text{s}$ $t_p = 200\text{ }\mu\text{s}$			200		μs

Package Y4				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal				300	A
T _{VJ}	virtual junction temperature			-40		125	°C
T _{op}	operation temperature			-40		100	°C
T _{stg}	storage temperature			-40		125	°C
Weight					150		g
M _D	mounting torque			2.25		2.75	Nm
M _T	terminal torque			4.5		5.5	Nm
d _{Spp/App}	creepage distance on surface striking distance through air	terminal to terminal	14.0	10.0			mm
d _{Spb/Apb}		terminal to backside	16.0	16.0			mm
V _{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA	3600			V
		t = 1 minute		3000			V



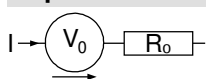
Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.# (33-36)

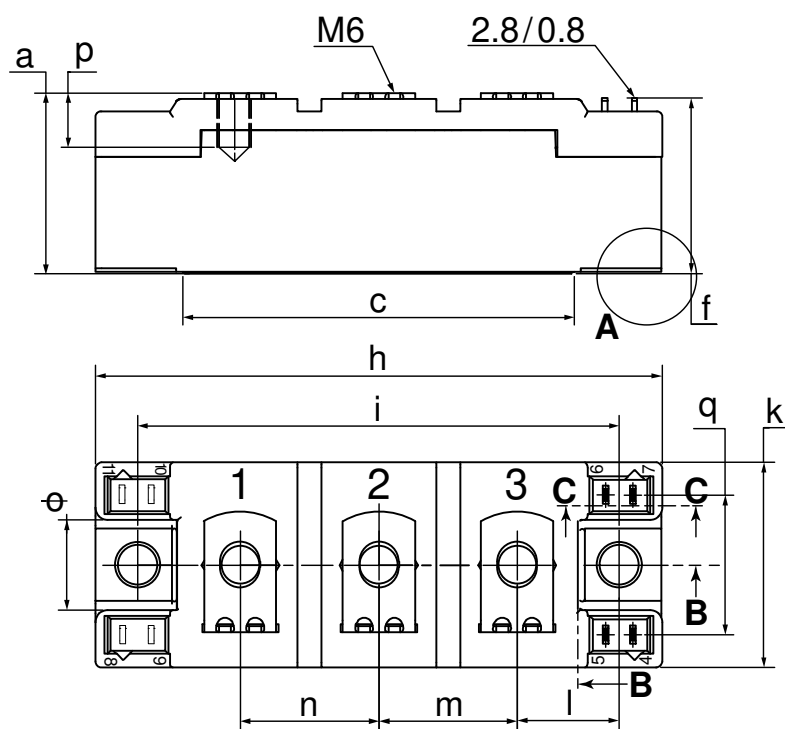
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCK200-18io1	MCK200-18io1	Box	6	509438

Equivalent Circuits for Simulation

* on die level

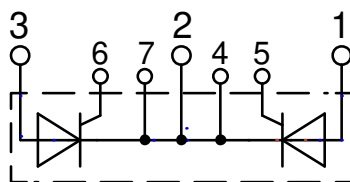
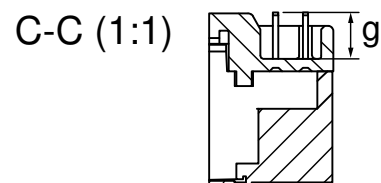
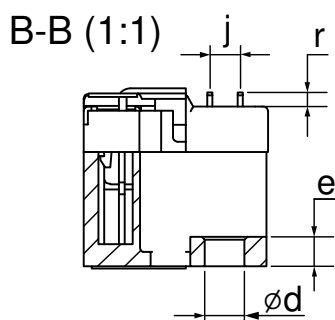
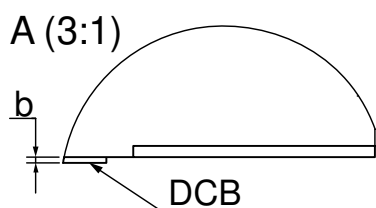
$T_{VJ} = 125^{\circ}\text{C}$

		Thyristor	
$V_{0\max}$	threshold voltage	0.8	V
$R_{0\max}$	slope resistance *	0.7	mΩ

Outlines Y4


Optional accessories for modules
 Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red
 Type ZY 180L (L = Left for pin pair 4/5)
 Type ZY 180R (R = Right for pin pair 6/7) } UL 758, style 3751

Dim.	MIN [mm]	MAX [mm]	MIN [inch]	MAX [inch]
a	30.0	30.6	1.181	1.205
b	typ. 0.25		typ. 0.010	
c	64.0	65.0	2.520	2.559
d	6.5	7.0	0.256	0.275
e	4.9	5.1	0.193	0.201
f	28.6	29.2	1.126	1.150
g	7.3	7.7	0.287	0.303
h	93.5	94.5	3.681	3.720
i	79.5	80.5	3.130	3.169
j	4.8	5.2	0.189	0.205
k	33.4	34.0	1.315	1.339
l	16.7	17.3	0.657	0.681
m	22.7	23.3	0.894	0.917
n	22.7	23.3	0.894	0.917
o	14.0	15.0	0.551	0.591
p	typ. 10.5		typ. 0.413	
q	22.8	23.3	0.898	0.917
r	1.8	2.4	0.071	0.041



Thyristor

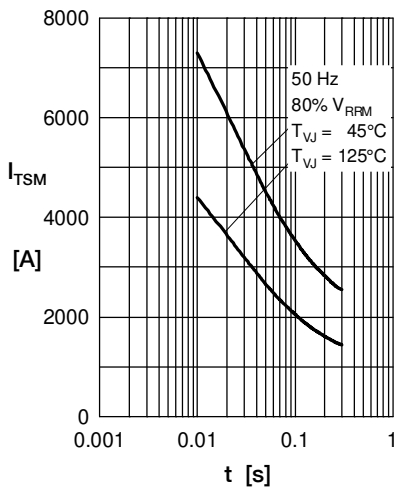


Fig. 1 Surge overload current I_{TSM} ,
 I_{FSM} : Crest value, t : duration

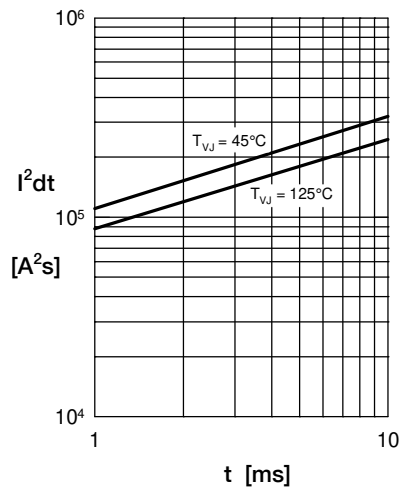


Fig. 2 I^2t versus time (1-10 ms)

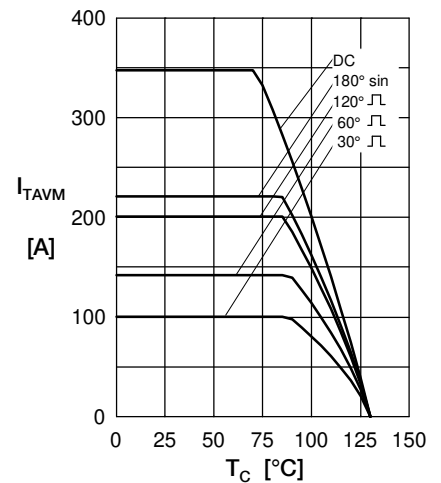


Fig. 3 Max. forward current
at case temperature

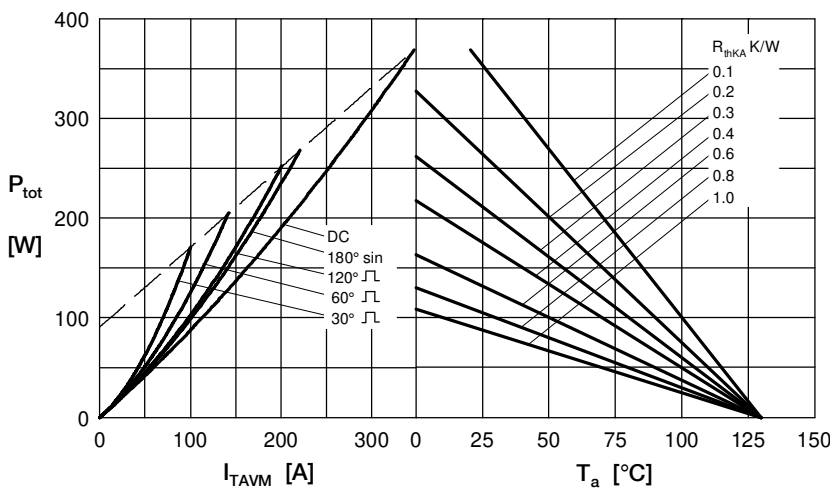


Fig. 4 Power dissipation vs. on-state current & ambient temperature
(per thyristor or diode)

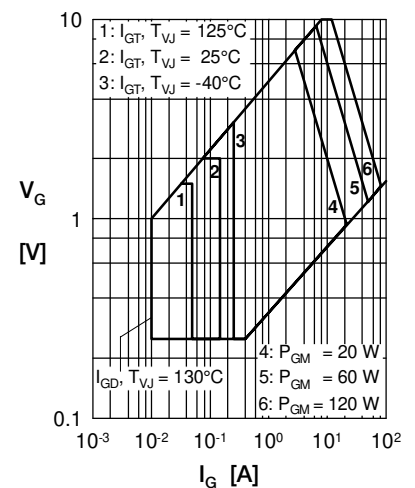


Fig. 5 Gate trigger characteristics

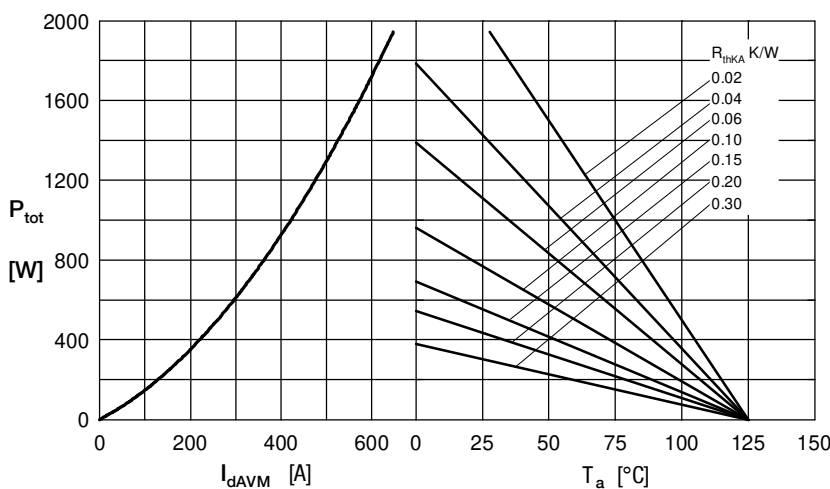


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct
output current and ambient temperature

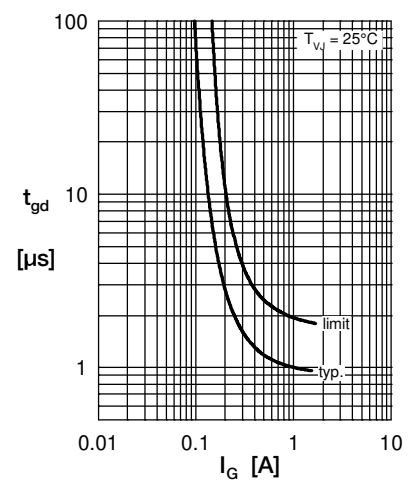


Fig. 7 Gate trigger delay time

Thyristor

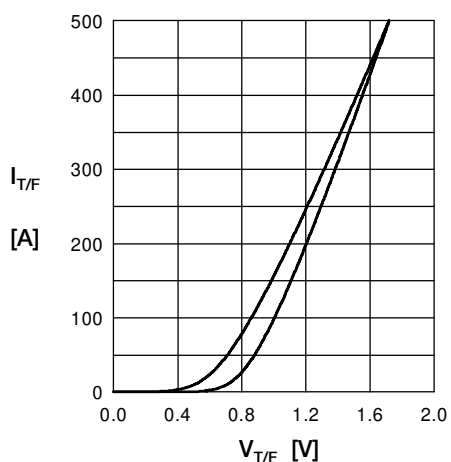
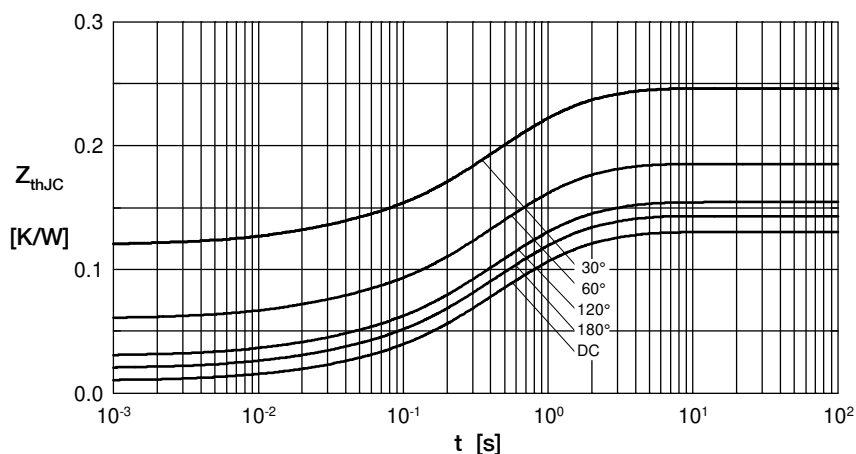


Fig. 8 Forward current versus voltage drop



Constants for Z_{thJC} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.0100	0.00014
2	0.0065	0.019
3	0.0250	0.180
4	0.0615	0.520
5	0.0270	1.600

Fig. 9 Transient thermal impedance junction to case at various conduction angles

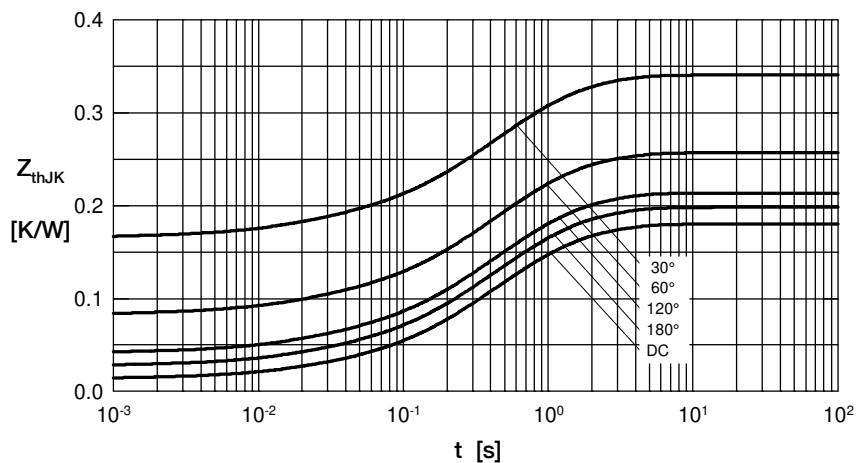


Fig. 10 Transient thermal impedance junction to heatsink (per thyristor/diode)